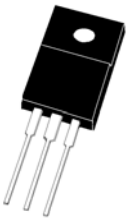
Switchmode
Full Plastic Dual Schottky Barrier Power Rectifiers

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

SCHOTTKY BARRIER RECTIFIERS

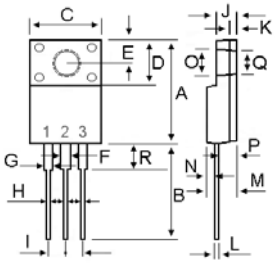
30 AMPERES
60 VOLTS



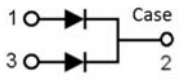
ITO-220AB

Features

- ＊Low Forward Voltage.
- ＊Low Switching noise.
- ＊High Current Capacity
- ＊Guarantee Reverse Avalanche.
- ＊Guard-Ring for Stress Protection.
- ＊Low Power Loss & High efficiency.
- ＊150℃ Operating Junction Temperature
- ＊Low Stored Charge Majority Carrier Conduction.
- ＊Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- ＊*Pb free*
- ＊*In compliance with EU RoHs directives*



DIM	MILLIMETERS	
	MIN	MAX
A	14.80	16.10
B	12.65	13.80
C	9.85	10.36
D	4.60	6.80
E	2.50	3.50
F	1.00	1.45
G	1.00	1.45
H	0.30	0.90
I	2.40	2.70
J	2.34	3.30
K	0.55	1.30
L	0.36	0.80
M	4.20	4.90
N	1.10	1.80
O	2.90	3.50
P	2.50	3.15
Q	2.90	3.50
R	3.10	4.85



MAXIMUM RATINGS

Characteristic	Symbol	SRF3060C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
RMS Reverse Voltage	$V_{R(RMS)}$	42	V
Average Rectifier Forward Current (Per dioed) Total Device (Rated V_R),T_C=100℃	$I_{F(AV)}$	15 30	A
Peak Repetitive Forward Current (Rate V_R, Square Wave, 20kHz)	I_{FM}	30	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I_{FSM}	250	A
Operating and Storage Junction Temperature Range	T_J , T_{STG}	-65 to +150	℃

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage (I_F =15 Amp T_C = 25℃) (I_F =15 Amp T_C = 125℃)	V_F	--- ---	0.63 0.58	0.70 ---	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T_C = 25℃) (Rated DC Voltage, T_C = 125℃)	I_R	--- ---	0.03 30	0.5 ---	mA
Typical Thermal Resistance junction to case	$R_{\theta jc}$		3.0		℃/w

FIG-1 FORWARD CURRENT DERATING CURVE

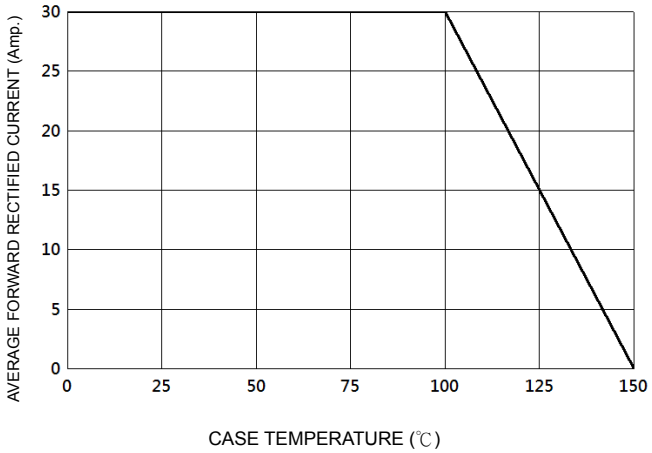


FIG-2 TYPICAL FORWARD CHARACTERISTICS

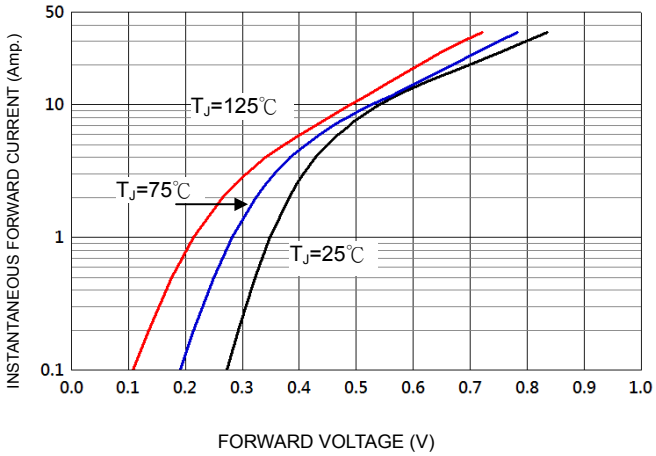


FIG-3 TYPICAL REVERSE CHARACTERISTICS

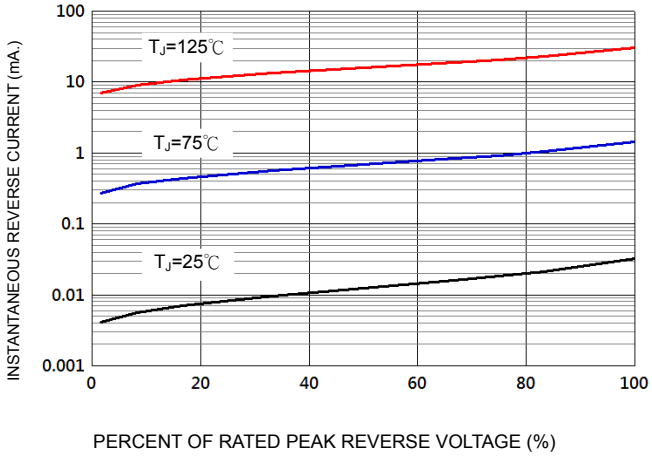


FIG-4 TYPICAL JUNCTION CAPACITANCE

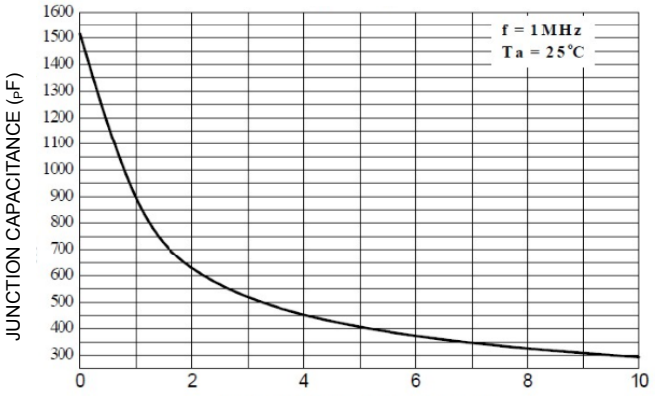
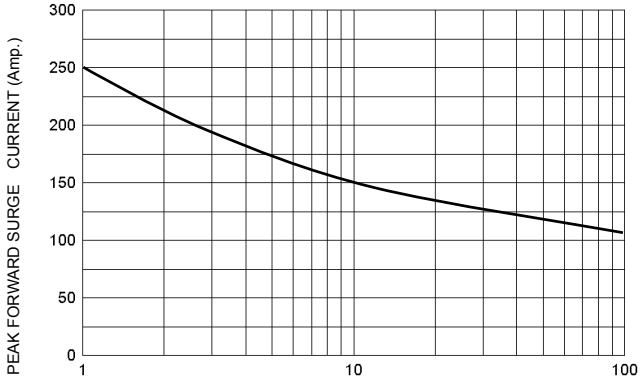


FIG-5 PEAK FORWARD SURGE CURRENT



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